

AlInGaP LED DICE

Part NO.: AOC-820YxM-Au Series

PRELIMINARY

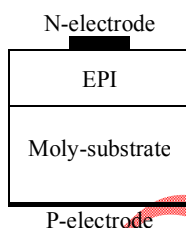
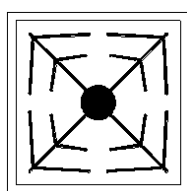
Features

- Yellow color emission
- Excellent performance & high efficiency
- Great reliability even in harsh environment
- Mirror reflector to increase efficiency

Description

AOC-820YxM series is a yellow color emitting AlInGaP LED grown by MOCVD technique. Its structure enables enhanced quantum efficiency; the mirror reflector greatly increases the light extraction efficiency and therefore a greater light intensity. This device is designed for ultra-high brightness (UHB) automobile, display, and consumer electronic applications.

Chip Dimensions



Emitting Area : 20mil×20mil ± 1mil

Bonding Pad : $\phi 100\mu\text{m} \pm 10\mu\text{m}$

Chip Thickness : $100\mu\text{m} \pm 10\mu\text{m}$

Electrical and Optics Characteristics

Measuring Item	Symbol	Condition	Min	Typ.	Max	Unit
Forward Voltage	V _F	I _F =150mA	1.75	-	2.60	V
Reverse Current	I _R	V _R =5V	-	-	1.0	μ A
Dominant Wavelength	λd	I _F =150mA	584	-	597	nm
Max. Junction Temperature	T _{max}	-	≤ 125			℃
Max. DC forward current	I _f	Ta = 25℃	≤ 150			mA
Storage temperature	T _{stg}	Chip on tape	0 ~ 40			℃
		Only chip	-40 ~ 80			

Available Dominate Wavelength and Iv Matrix

Part No.	Wavelength	$\geq 5000\text{mcd}$	$\geq 5500\text{mcd}$	$\geq 6000\text{mcd}$	$\geq 6500\text{mcd}$
820 YxM	584 ~ 597 nm	Y500	Y550	Y600	Y650

Note:

1. All measurements are done with AOC's standard testing equipment.
2. Luminance intensity is measured on bare chip.
3. Above contents are subject to change without notice.
4. Special requests are also welcome, please contact AOC's sale representative for any request.
5. Characteristics curves are measured within TO-46 package, different result may caused by packaging method.
6. The IV Bin Y500 is comparable to Epistar PX20 6300mcd.